General Description

The AGM16N10C combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
100V	15mΩ	55A

TO-220 Pin Configuration

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM16N10C	AGM16N10C	TO-220	---	---	1000

Table 1. Absolute Maximum Ratings (TA=25℃)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	100	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25℃) **(Note 1)**	55	A
	Drain Current-Continuous(Tc=100℃)	37	A
IDM (pluse)	Drain Current-Pulsed **(Note 2)**	220	A
PD	Maximum Power Dissipation(Tc=25℃)	103	w
	Maximum Power Dissipation(Tc=100℃)	41	w
EAS	Avalanche energy **(Note 3)**	37	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	℃

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State)[1]	---	60	℃/W
RθJC	Thermal Resistance Junction-Case[1]	---	1.2	℃/W

Table 3. Electrical Characteristics (TJ=25℃unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	100	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=100V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	1.2	--	2.2	V
gFS	Forward Transconductance	VDS=5V,ID=8A	--	38	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=12A	--	15	16.5	mΩ
		VGS=4.5V, ID=8A	--	19	22	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=40V,VGS=0V, F=1MHZ	--	930	--	pF
Coss	Output Capacitance		--	280	--	pF
Crss	Reverse Transfer Capacitance		--	9.8	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	1.2	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V,VDS=50V, RGEN=10Ω	--	10	--	nS
tr	Turn-on Rise Time		--	24	--	nS
td(off)	Turn-Off Delay Time		--	16	--	nS
tf	Turn-Off Fall Time		--	5.0	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=50V, ID=20A	--	24	--	nC
Qgs	Gate-Source Charge		--	1.5	--	nC
Qgd	Gate-Drain Charge		--	13	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	55	A
VSD	Forward on Voltage	VGS=0V,IS=12A	--	--	1.2	V
trr	Reverse Recovery Time	IF=12A , dI/dt=100A/μs , TJ=25℃	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25℃

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

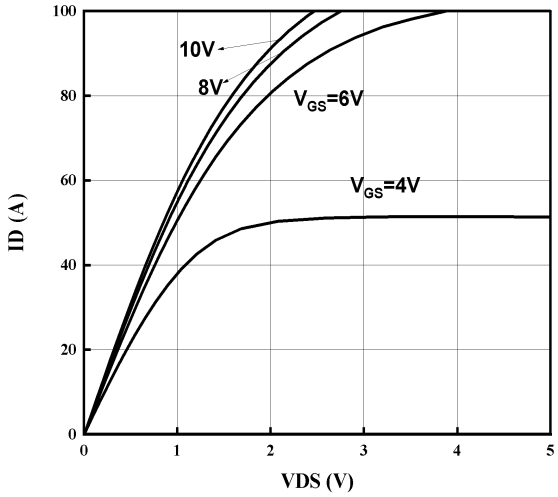


Fig1. Typical Output Characteristics

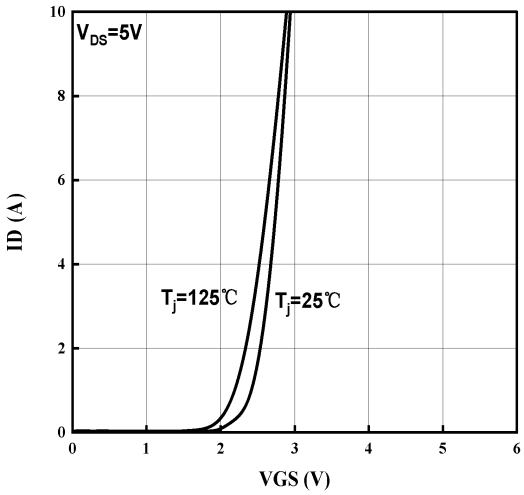


Fig2. Typical Transfer Characteristics

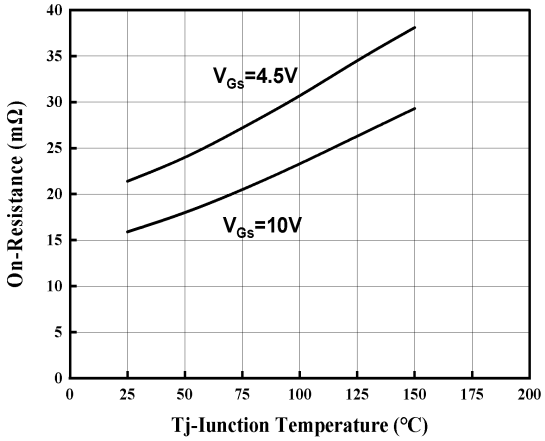


Fig3. On-Resistance Vs. Temperature

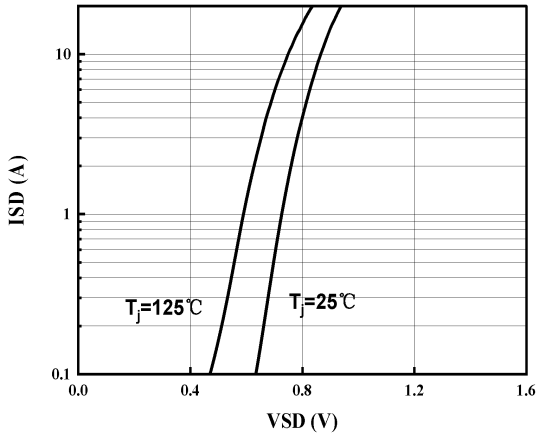


Fig4. Typical Source-Drain Diode Forward Voltage

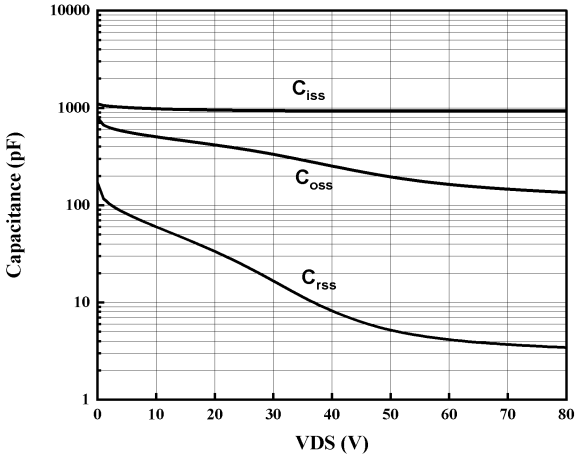


Fig5. Typical.Capacitance

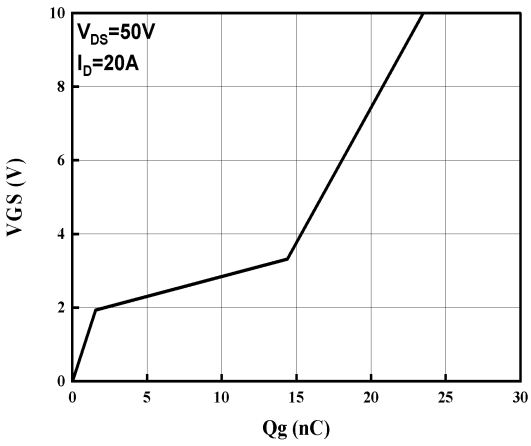


Fig6. Typical.Gate Charge

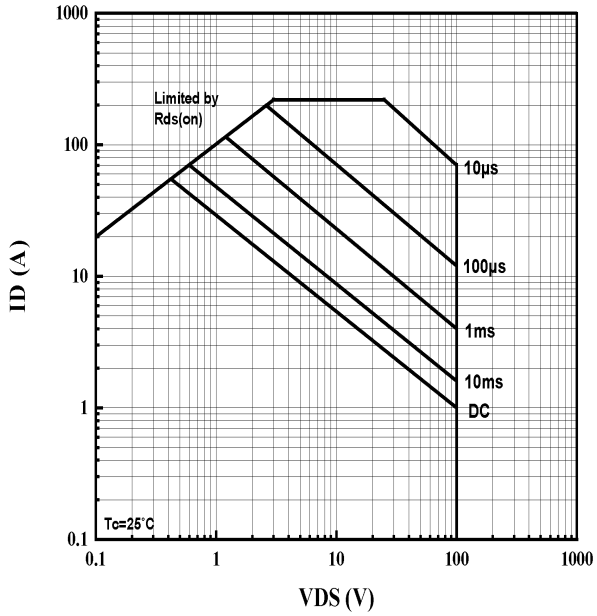


Fig7. Safe Operating Area

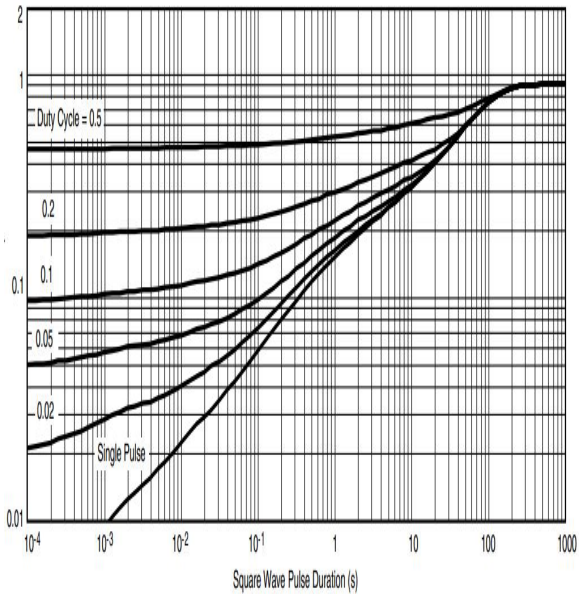
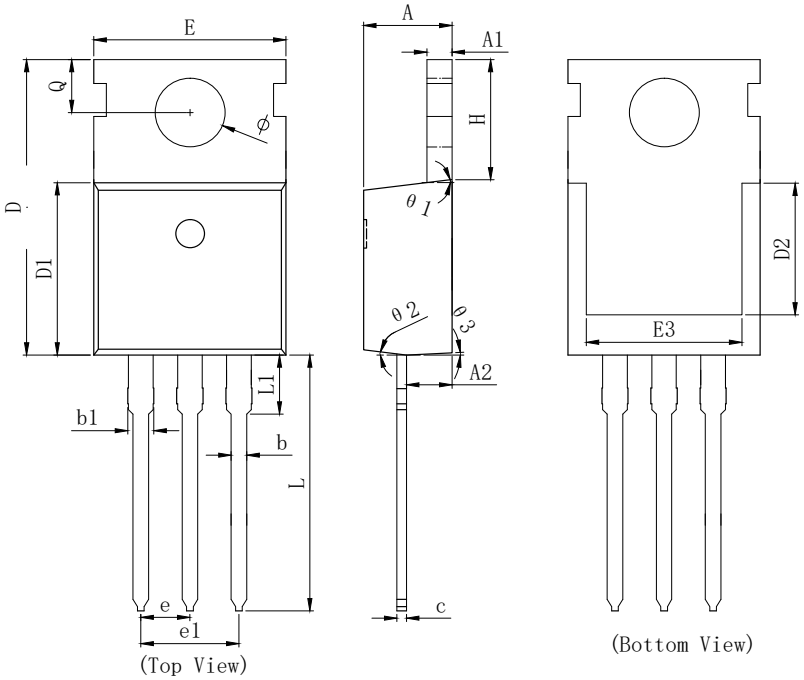


Fig8. Normalized transient thermal impedance

TO-220 PACKAGE INFORMATION



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	4.370	4.570	4.700
A1	1.250	1.300	1.400
A2	2.150	2.350	2.550
b	0.700	0.800	0.950
b1	1.170	1.270	1.470
c	0.450	0.500	0.600
D	15.100	15.600	16.100
D1	8.800	9.100	9.400
D2	5.500	6.300 REF	
E	9.700	10.000	10.300
E3	7.000	7.600 REF	
e	2.540 BSC		
e1	5.080 BSC		
L	13.200	13.500	13.800
L1		3.100	3.400
H	6.250	6.500	6.750
Φ	3.400	3.600	3.800
Q	2.600	2.800	3.000
θ1	7° TYP		
θ2	7° TYP		
θ3	3° TYP		

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This document is the first version issued on Dec.10th, 2023. This document replaces all previously provided information.

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